

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	70	pixel with TFT same grain adj size	US-PGPUB; USPAT	OR	ON	2005/08/03 10:24
L2	30	peak-to-valley same (leak leakage) adj current	US-PGPUB; USPAT	OR	ON	2005/08/03 10:25
L3	17	peak-to-valley same (leak leakage) adj current and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:26
L4	71807	peak-to-valley same (switching adj speed) current and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
L5	0	peak-to-valley same (switching adj speed) and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
L6	0	peak-to-valley same (switch\$ adj speed) and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
L7	12	peak-to-valley and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:30
L8	510	(roughness peak-to-valley) and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:30
L9	508	roughness and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:31
L10	409	roughness and (polysilicon polycrystalline) and (TFT "thin film transistor") and (speed current)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:32
L11	53	roughness same (speed current) and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:48
L12	2	10/226110	US-PGPUB; USPAT	OR	ON	2005/08/03 10:49
L13	3	10/226110 "6621103".pn.	US-PGPUB; USPAT	OR	ON	2005/08/03 10:50
L14	5	10/226110 10/112929	US-PGPUB; USPAT	OR	ON	2005/08/03 12:19
L15	1	"20020102823"	US-PGPUB; USPAT	OR	ON	2005/08/03 12:25
L16	772	grain adj diameter with nm	US-PGPUB; USPAT	OR	ON	2005/08/03 12:26
L17	212	L16 and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:27

L18	28	(US-20030107564-\$ or US-20040257486-\$ or US-20040038600-\$ or US-20050112850-\$ or US-20020142567-\$ or US-20040115953-\$ or US-20040259326-\$ or US-20040145001-\$ or US-20020102823-\$ or US-20020158829-\$ or US-20030049874-\$ or US-20050140283-\$ or US-20050088381-\$ or US-20040038501-\$ or US-20040171236-\$).did. or (US-6476788-\$ or US-6535257-\$ or US-6740938-\$ or US-6636280-\$ or US-6586791-\$ or US-6911698-\$ or US-6806498-\$ or US-6716726-\$ or US-6690064-\$ or US-5851440-\$ or US-6887724-\$ or US-6479837-\$ or US-6621103-\$).did.	US-PGPUB; USPAT	OR	ON	2005/08/03 12:28
L19	20	L18 and (grain adj (size diameter))	US-PGPUB; USPAT	OR	ON	2005/08/03 12:34
L20	6759	grain adj size and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:35
L21	3148	L20 and (transistor TFT)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:34
L22	1662	large with grain adj size and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:38
L23	948	L22 and (transistor TFT)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:35
L24	225	large with grain adj diameter and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:40
L25	212	grain adj diameter with nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:53
L26	7	grain adj diameter with ("900" "800" "700" "600") adj nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:56
L27	40	grain adj size with ("900" "800" "700" "600") adj nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 13:13
L28	0	grain adj size with ("900" "800" "700" "600") and large adj nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 13:14
L29	26	grain adj size with (large and ("900" "800" "700" "600") adj nm)) and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 13:30

L30	1	"20020158298"	US-PGPUB; USPAT	OR	ON	2005/08/03 13:36
L31	1	"20040038438"	US-PGPUB; USPAT	OR	ON	2005/08/03 13:47
L32	1	"6479837".pn.	US-PGPUB; USPAT	OR	ON	2005/08/03 13:47
L33	1	"20040038438"	US-PGPUB; USPAT	OR	ON	2005/08/03 13:56
S1	16	((first adj type) and (second adj type)) adj4 (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/02 09:17
S2	1	10/772431	US-PGPUB; USPAT	OR	ON	2005/08/02 09:43
S3	0	"2001376587"	US-PGPUB; USPAT; JPO	OR	ON	2005/08/02 09:43
S4	1	"2001-376587"	US-PGPUB; USPAT; JPO	OR	ON	2005/08/02 09:44
S5	0	"376587"	JPO	OR	ON	2005/08/02 09:44
S6	0	"2001376587"	JPO	OR	ON	2005/08/02 09:44
S7	0	"20010376587"	JPO	OR	ON	2005/08/02 09:48
S8	318	miyazawa-toshio.in.	JPO	OR	ON	2005/08/02 09:44
S9	0	JP20010376587	JPO	OR	ON	2005/08/02 09:48
S10	1	JP2001376587	JPO	OR	ON	2005/08/02 10:49
S11	1	JP2003176281	JPO	OR	ON	2005/08/02 10:51
S12	1565	tai-mitsuharu.in. mutsuko-hatano.in. yamaguchi-shinya.in. shiba-kodaira.in. sato-hideo.in.	JPO	OR	ON	2005/08/02 10:53
S14	325	S13 and hitachi.as.	JPO	OR	ON	2005/08/02 10:53
S15	244	tai-mitsuharu.in. mutsuko-hatano.in. yamaguchi-shinya.in. shiba-kodaira.in. sato-hideo.in.	US-PGPUB; USPAT	OR	ON	2005/08/02 10:54
S16	264	tai-mitsuharu.in. hatano-mutsuko.in. yamaguchi-shinya.in. shiba-kodaira.in. sato-hideo.in.	US-PGPUB; USPAT	OR	ON	2005/08/02 10:55
S17	190	S16 and @pd<"20030206"	US-PGPUB; USPAT	OR	ON	2005/08/02 10:57
S18	690	peak-to-valley with height	US-PGPUB; USPAT	OR	ON	2005/08/02 14:12
S19	145	S18 and thin adj film	US-PGPUB; USPAT	OR	ON	2005/08/02 10:57
S20	0	peak-to-valley with "20nm"	US-PGPUB; USPAT	OR	ON	2005/08/02 14:12

S21	122	peak-to-valley with "20"	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
S22	1206	349/43.ccls.	US-PGPUB; USPAT	OR	ON	2005/08/02 14:15
S23	2	S22 and ((peak adj2 valley) peak-to-valley)	US-PGPUB; USPAT	OR	ON	2005/08/02 14:16
S24	158	((peak adj2 valley) peak-to-valley) and (TFT (thin adj film adj transistor))	US-PGPUB; USPAT	OR	ON	2005/08/02 14:24
S25	67	((peak adj2 valley) peak-to-valley) and (TFT (thin adj film adj transistor)) and polycrystalline	US-PGPUB; USPAT	OR	ON	2005/08/02 14:33
S26	2	((peak adj2 valley) peak-to-valley) and 349/43.ccls.	US-PGPUB; USPAT	OR	ON	2005/08/02 14:33
S27	4	((peak with valley) peak-to-valley) and 349/43.ccls.	US-PGPUB; USPAT	OR	ON	2005/08/02 18:07
S28	104	((peak with valley) peak-to-valley) and grain adj size and polycrystalline	US-PGPUB; USPAT	OR	ON	2005/08/02 15:51
S29	35	((peak with valley) peak-to-valley) and grain adj size and polycrystalline and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/02 15:52
S30	7	("5270567" "5757445" "5798744" "5851440" "5926702" "6011277" "6211553").PN. OR ("6476788"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:03
S31	205	peak-to-valley adj height and current	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:58
S32	3	S31 and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:05
S33	108	polycrystalline and grain adj diameter and orientation and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:43
S34	508	polycrystalline and grain adj size and orientation and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:43
S35	44	polycrystalline and (grain adj size) with ("100" adj nm)and orientation and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:47
S36	2	10/143192	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:45

S37	4	09/790545	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:31
S38	5	peak-to-valley adj height with "5" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:58
S39	0	peak-to-valley adj height with "4" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59
S40	0	peak-to-valley adj height with "3" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59
S41	0	peak-to-valley adj height with "1" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59
S42	1	peak-to-valley adj height with "2" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59
S43	492	((peak with valley) peak-to-valley) with "nm"	US-PGPUB; USPAT	OR	ON	2005/08/02 18:07
S44	35	S43 and "thin film transistor"	US-PGPUB; USPAT	OR	ON	2005/08/02 18:07
S45	7	polycrystalline adj silicon and grain adj size and peak-to-valley	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:34
S46	145	grain with scanning adj direction	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:34
S47	127	S46 and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:34